

IN THE CLAIMS

Claims 1 through 26 are pending in this application. Please cancel claims 1-7, 10-16, and 23-26 without prejudice or disclaimer, and amend the remaining claims, as follows:

Claims 1 – 7 (canceled)

8. (currently amended) An active matrix display device comprising:

a substrate having a gate signal line and a drain signal line;

a thin film transistor that is driven being supplied with a scanning signal from the gate signal line, the thin-film transistor having a gate electrode that is made of a material different than the gate signal line and has a part of which is directly laid on or under the gate signal line to establish electrical connection, and

a pixel electrode that is supplied with a video signal from the drain signal line via the thin-film transistor ~~The active matrix display device according to claim 1,~~

wherein thin film metal layers are formed on a drain region and a source region, respectively, of the first thin-film transistor and/or each of the second thin-film transistors, and portions of the respective said thin film metal layers are exposed through respective contact holes that are formed through a passivation film that covers thin-film transistor.

9. (original) The active matrix display device according to claim 8, wherein the metal layers are formed at the same time as a gate electrode of the thin-film transistor is formed.

Claims 10 – 16 (canceled)

17. (currently amended) An active matrix display device comprising:

a substrate having a gate signal line and a drain signal line;

a thin film transistor that is driven being supplied with a scanning signal from the gate signal line, the thin-film transistor having a gate electrode that is made of a material different than the gate signal line and has a part of which is electrically connected to the gate signal line, and

a pixel electrode that is supplied with a video signal from the drain signal line via the thin-film transistor ~~The active matrix display device according to claim 2,~~

wherein thin film metal layers are formed on a drain region and a source region, respectively, of the first thin-film transistor and/or each of the second thin-film transistors, and portions of the respective said thin film metal layers are exposed through respective contact holes that are formed through a passivation film that covers thin-film transistor.

18. (currently amended) An active matrix display device comprising:

a substrate having a gate signal line and a drain signal line;

a thin-film transistor that is driven being supplied with a scanning signal from the gate signal line, the thin-film transistor having a gate electrode that is made of a material different than the gate signal line and that overlaps with the gate signal line, and

a pixel electrode that is supplied with a video signal from the drain signal line via the thin-film transistor ~~The active matrix display device according to claim 3,~~

wherein thin film metal layers are formed on a drain region and a source region, respectively, of the first thin-film transistor and/or each of the second thin-film transistors, and portions of the respective said thin film metal layers are exposed through respective contact holes that are formed through a passivation film that covers thin-film transistor.

19. (currently amended) An active matrix display device comprising:

a substrate having a gate signal line and a drain signal line;

a thin-film transistor that is driven being supplied with a scanning signal from the gate signal line, the thin-film transistor having a gate electrode having a portion that is made of a layer different than the gate signal line and that is electrically connected to the gate signal line, and

a pixel electrode that is supplied with a video signal from the drain signal line via the thin-film transistor ~~The active matrix display device according to claim 4.~~

wherein thin film metal layers are formed on a drain region and a source region, respectively, of the first thin-film transistor and/or each of the second thin film transistors, and portions of the respective said thin film metal layers are exposed through respective contact holes that are formed through a passivation film that covers thin-film transistor.

20. (previously presented) The active matrix display device according to claim 17, wherein the metal layers are formed at the same time as a gate electrode of the thin-film transistor is formed.
21. (previously presented) The active matrix display device according to claim 18, wherein the metal layers are formed at the same time as a gate electrode of the thin-film transistor is formed.
22. (previously presented) The active matrix display device according to claim 19, wherein the metal layers are formed at the same time as a gate electrode of the thin-film transistor is formed.

Claims 23 – 26 (canceled)